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# PDTA144VMB



PNP resistor-equipped transistor; R1 = 47 kΩ, R2 = 10 kΩ Rev. 1 — 26 June 2012 Product data s

Product data sheet

### **Product profile**

### 1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC144VMB.

#### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

### 1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	33	47	61	kΩ
R2/R1	bias resistor ratio		0.17	0.21	0.26	



### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	3
3	0	output (collector)	2 3	1 R1
		Transparent top view		
			DFN1006B-3 (SOT883B)	sym003

## 3. Ordering information

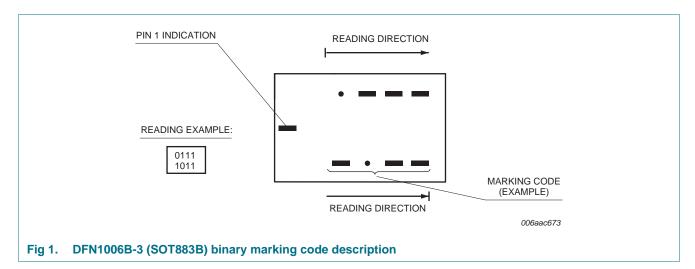
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PDTA144VMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

### 4. Marking

Table 4. Marking codes

Type number	Marking code
PDTA144VMB	0010 1101



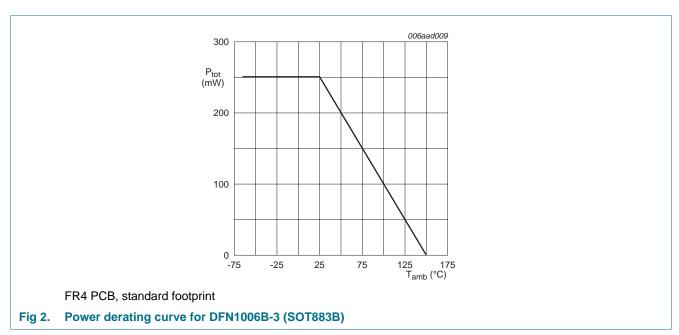
### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
$V_{CEO}$	collector-emitter voltage	open base		-	-50	V
$V_{EBO}$	emitter-base voltage	open collector		-	-15	V
V <sub>I</sub>	input voltage	positive		-	15	V
		negative		-	-40	V
Io	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

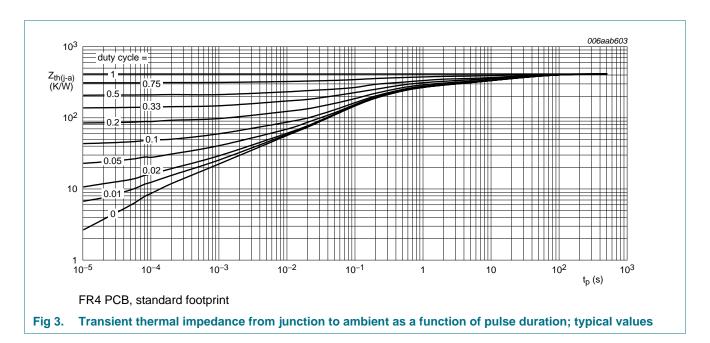
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTA144VMB

**Product data sheet** 

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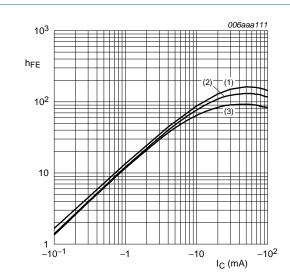


### 7. Characteristics

Table 7. Characteristics

Parameter	Conditions		Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
	$V_{CE}$ = -30 V; $I_B$ = 0 A; $T_{amb}$ = 25 °C		-	-	-1	μΑ
current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	-5	μΑ
emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	-150	μΑ
DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -5 mA; $T_{amb}$ = 25 °C		40	-	-	
collector-emitter saturation voltage	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
off-state input voltage	$V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu$ A; $T_{amb}$ = 25 °C		-	-3.1	-1	V
on-state input voltage	$V_{CE}$ = -0.3 V; $I_{C}$ = -2 mA; $T_{amb}$ = 25 °C		-6	-3.8	-	V
bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		33	47	61	kΩ
bias resistor ratio			0.17	0.21	0.26	
collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$		-	-	2	pF
transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$	[1]	-	180	-	MHz
	current  collector-emitter cut-off current  emitter-base cut-off current  DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance	current culter cut-off current $V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_{amb} = 25 \text{ °C}$ $V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_j = 150 \text{ °C}$ emitter-base cut-off current $V_{CE} = -30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C}$ current $V_{CE} = -5 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C}$ collector-emitter saturation voltage $V_{CE} = -5 \text{ V}; \ I_C = -5 \text{ mA}; \ T_{amb} = 25 \text{ °C}$ con-state input voltage $V_{CE} = -5 \text{ V}; \ I_C = -100 \text{ µA}; \ T_{amb} = 25 \text{ °C}$ on-state input voltage $V_{CE} = -5 \text{ V}; \ I_C = -100 \text{ µA}; \ T_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $V_{CE} = -0.3 \text{ V}; \ I_C = -2 \text{ mA}; \ T_{amb} = 25 \text{ °C}$ bias resistor ratio collector capacitance $V_{CB} = -10 \text{ V}; \ I_E = 0 \text{ A}; \ I$	current collector-emitter cut-off current $V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_{amb} = 25 \text{ °C}$ current $V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_j = 150 \text{ °C}$ emitter-base cut-off current $V_{EB} = -5 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C}$ current gain $V_{CE} = -5 \text{ V}; \ I_C = -5 \text{ mA}; \ T_{amb} = 25 \text{ °C}$ collector-emitter $I_C = -10 \text{ mA}; \ I_B = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C}$ saturation voltage off-state input voltage $V_{CE} = -5 \text{ V}; \ I_C = -100 \text{ µA}; \ T_{amb} = 25 \text{ °C}$ on-state input voltage $V_{CE} = -0.3 \text{ V}; \ I_C = -2 \text{ mA}; \ T_{amb} = 25 \text{ °C}$ bias resistor 1 (input) $V_{CE} = -0.3 \text{ V}; \ I_C = -0.$	$ \begin{array}{c} \text{current} \\ \text{collector-emitter cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} V_{CE} = -30 \text{ V};  I_{B} = 0 \text{ A};  T_{amb} = 25 \text{ °C} \\ \hline V_{CE} = -30 \text{ V};  I_{B} = 0 \text{ A};  T_{j} = 150 \text{ °C} \\ \hline V_{CE} = -30 \text{ V};  I_{B} = 0 \text{ A};  T_{j} = 150 \text{ °C} \\ \hline V_{CE} = -30 \text{ V};  I_{C} = 0 \text{ A};  T_{amb} = 25 \text{ °C} \\ \hline \text{current} \\ \end{array} \begin{array}{c} - 0.5 \text{ mA};  V_{amb} = 25 \text{ °C} \\ \hline \text{current} \\ \end{array} \begin{array}{c} - 0.5 \text{ mA};  V_{amb} = 25 \text{ °C} \\ \hline \text{collector-emitter} \\ \hline \text{saturation voltage} \\ \hline \text{off-state input voltage} \\ \hline \text{off-state input voltage} \\ \hline \text{off-state input voltage} \\ \hline \text{V}_{CE} = -5 \text{ V};  I_{C} = -100  \mu\text{A};  V_{amb} = 25 \text{ °C} \\ \hline \text{on-state input voltage} \\ \hline \text{V}_{CE} = -0.3 \text{ V};  I_{C} = -2 \text{ mA};  V_{amb} = 25 \text{ °C} \\ \hline \text{bias resistor 1 (input)} \\ \hline \text{T}_{amb} = 25 \text{ °C} \\ \hline \text{bias resistor ratio} \\ \hline \text{collector capacitance} \\ \hline \text{V}_{CB} = -10 \text{ V};  I_{E} = 0 \text{ A};  I_{E} = 0  A$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c} \text{collector-base cut-off current} & V_{CB} = -50 \text{ V}; \ I_E = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} & - & - & -100 \\ \hline \text{current} & V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} & - & - & -1 \\ \hline \text{current} & V_{CE} = -30 \text{ V}; \ I_B = 0 \text{ A}; \ T_{j} = 150 \text{ °C} & - & - & -5 \\ \hline \text{emitter-base cut-off current} & V_{EB} = -5 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} & - & - & -150 \\ \hline \text{current} & V_{CE} = -5 \text{ V}; \ I_C = -5 \text{ mA}; \ T_{amb} = 25 \text{ °C} & 40 & - & - \\ \hline \text{collector-emitter} & I_{C} = -10 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} & - & - & -150 \\ \hline \text{collector-emitter} & I_{C} = -10 \text{ mA}; \ I_{B} = -0.5 \text{ mA}; \ T_{amb} = 25 \text{ °C} & - & - & -150 \\ \hline \text{off-state input voltage} & V_{CE} = -5 \text{ V}; \ I_{C} = -100 \text{ µA}; \ T_{amb} = 25 \text{ °C} & - & -3.1 & -1 \\ \hline \text{on-state input voltage} & V_{CE} = -0.3 \text{ V}; \ I_{C} = -2 \text{ mA}; \ T_{amb} = 25 \text{ °C} & -6 & -3.8 & - \\ \hline \text{bias resistor 1 (input)} & T_{amb} = 25 \text{ °C} & 33 & 47 & 61 \\ \hline \text{bias resistor ratio} & V_{CB} = -10 \text{ V}; \ I_{E} = 0 \text{ A}; \ I_{E$

<sup>[1]</sup> Characteristics of built-in transistor.



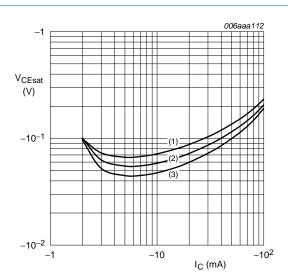
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



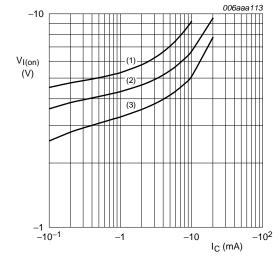
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



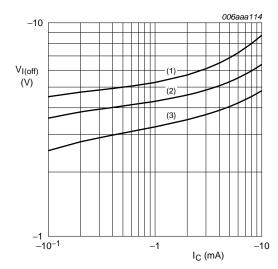
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

PDTA144VMB

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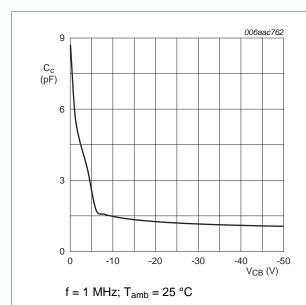


Fig 8. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor

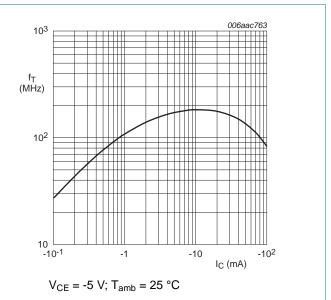


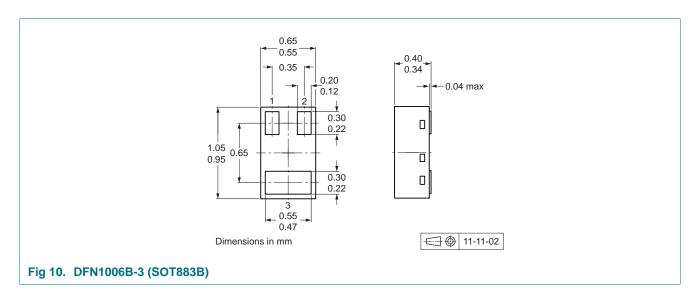
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

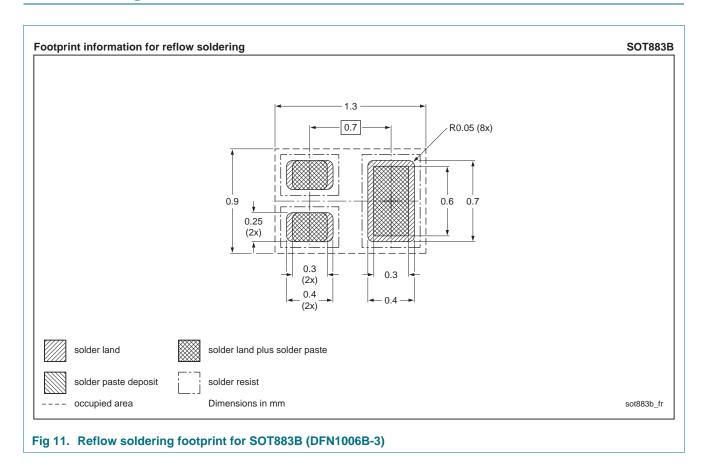
### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

### 9. Package outline



### 10. Soldering





## 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA144VMB v.1	20120626	Product data sheet	-	-

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### 12. Legal information

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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## PDTA144VMB

PNP resistor-equipped transistor; R1 = 47 k $\Omega$ , R2 = 10 k $\Omega$ 

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